

SWITCHING REGULATOR APPLICATIONS

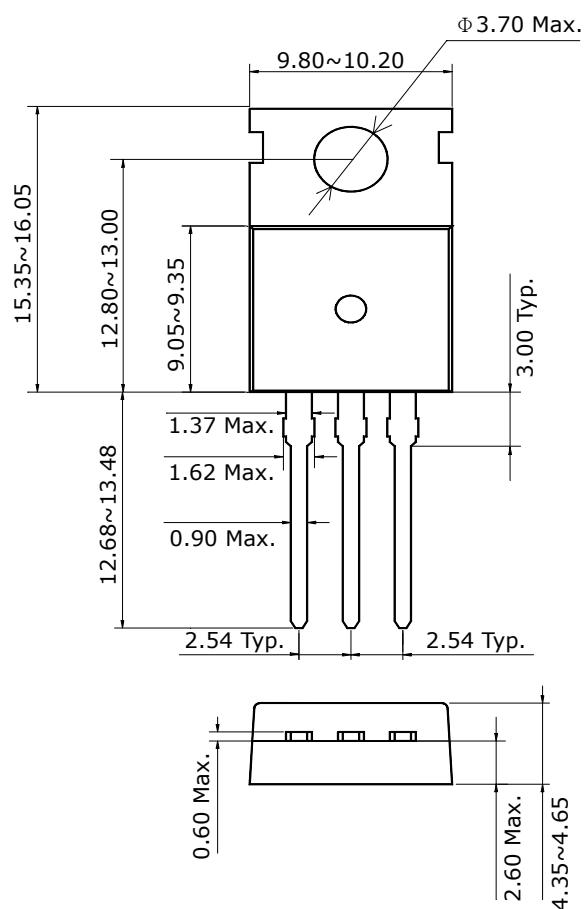
Features

- High Voltage: $BV_{DSS}=80V$ (Min.)
- Low C_{rss} : $C_{rss}=220pF$ (Typ.)
- Low gate charge : $Q_g=80nC$ (Typ.)
- Low $R_{DS(on)}$: $R_{DS(on)}=17m\Omega$ (Max.)

Ordering Information

| Type NO. | Marking | Package Code |
|----------|---------|--------------|
| STK7508P | STK7508 | TO-220AB-3L |

Outline Dimensions

unit : mm

PIN Connections

1. Gate
2. Drain
3. Source

Absolute maximum ratings (Tc=25°C)

| Characteristic | Symbol | Rating | Unit |
|-------------------------------------|------------------|---------|------|
| Drain-Source voltage | V _{DSS} | 80 | V |
| Gate-Source voltage | V _{GSS} | ±20 | V |
| Continuous Drain current (Tc=25°C) | I _D | 75 | A |
| Continuous Drain current (Tc=100°C) | I _D | 54.3 | A |
| Drain Current-Pulsed ① | I _{DM} | 300 | A |
| Power Dissipation (Tc=25°C) | P _D | 220 | W |
| Single Pulsed Avalanche Energy ② | E _{AS} | 1310 | mJ |
| Avalanche current ① | I _{AR} | 75 | A |
| Repetitive Avalanche Energy ① | E _{AR} | 17.3 | mJ |
| Junction temperature | T _J | 175 | °C |
| Storage temperature range | T _{stg} | -55~175 | |

Thermal Resistance

| Characteristic | Symbol | Typ. | Max | Units |
|---------------------|----------------------|------|------|-------|
| Junction to Case | R _{th(J-C)} | - | 0.68 | °C/W |
| Junction to Ambient | R _{th(J-a)} | - | 62.5 | |

Electrical Characteristics (Tc=25°C)

| Characteristic | Symbol | Test Condition | Min. | Typ. | Max. | Unit |
|--------------------------------|---------------------|--|------|------|------|------|
| Drain-Source breakdown voltage | BV _{DSS} | I _D =250μA, V _{GS} =0 | 80 | - | - | V |
| Gate-Threshold voltage | V _{GS(th)} | I _D =250μA, V _{DS} = V _{GS} | 2.0 | - | 4.0 | V |
| Drain-source leakage current | I _{DSS} | V _{DS} =80V, V _{GS} =0V | - | - | 10 | μA |
| Gate-source leakage | I _{GSS} | V _{DS} =0V, V _{GS} =±20V | - | - | ±100 | nA |
| Drain-Source on-resistance ③ | R _{DS(ON)} | V _{GS} =10V, I _D =37.5A | - | 14 | 17 | mΩ |
| Forward transfer admittance ③ | g _{fs} | V _{DS} =20V, I _D =37.5A | - | 15 | - | S |
| Input capacitance | C _{iss} | V _{GS} =0V, V _{DS} =25V, f=1MHz | - | 2540 | 3210 | pF |
| Output capacitance | C _{oss} | | - | 950 | 1200 | |
| Reverse transfer capacitance | C _{rss} | | - | 220 | 275 | |
| Turn-on delay time | t _{d(on)} | V _{DD} =40V, I _D =75A R _G =25Ω | - | 40 | 80 | ns |
| Rise time | t _r | | - | 230 | 460 | |
| Turn-off delay time | t _{d(off)} | | - | 170 | 340 | |
| Fall time | t _f | | - | 190 | 330 | |
| Total gate charge | Q _g | V _{DS} =60V, V _{GS} =10V, I _D =75A | - | 80 | 105 | nC |
| Gate-source charge | Q _{gs} | | - | 16 | - | |
| Gate-drain("Miller")charge | Q _{gd} | | - | 30 | - | |

Source-Drain Diode Ratings and Characteristics (Tc=25°C)

| Characteristic | Symbol | Test Condition | Min | Typ | Max | Units |
|---------------------------|-----------------|--|-----|-----|-----|-------|
| Continuous source current | I _S | Integral reverse diode in the MOSFET | - | - | 75 | A |
| Pulsed-source current ① | I _{SM} | | - | - | 300 | |
| Diode forward voltage ④ | V _{SD} | V _{GS} =0V, I _S =75A | - | - | 1.5 | V |
| Reverse recovery time | t _{rr} | I _S =75A di _F /dt=100A/us | - | 90 | - | ns |
| Reverse recovery charge | Q _{rr} | | - | 250 | - | uC |

Note :

- ① Repetitive Rating : Pulse Width Limited by Maximum Junction Temperature
- ② L=0.32mH I_{AS}=75A, V_{DD}=25V, R_G=25Ω , starting T_j=25 °C
- ③ Pulse Test : Pulse Width < 300us, Duty cycle≤ 2%
- ④ Essentially independent of operating temperature

Electrical Characteristic Curves

Fig. 1 I_D - V_{DS}

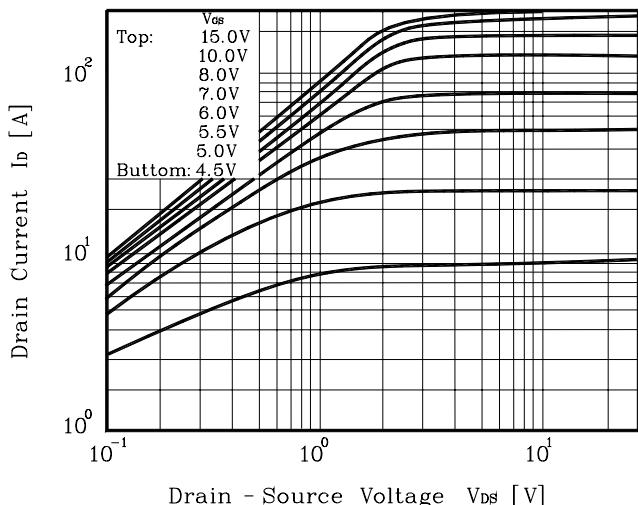


Fig. 2 I_D - V_{GS}

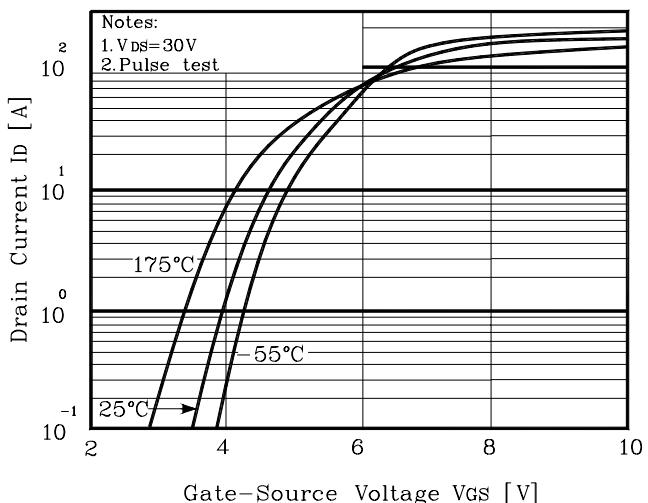


Fig. 3 $R_{DS(on)}$ - I_D

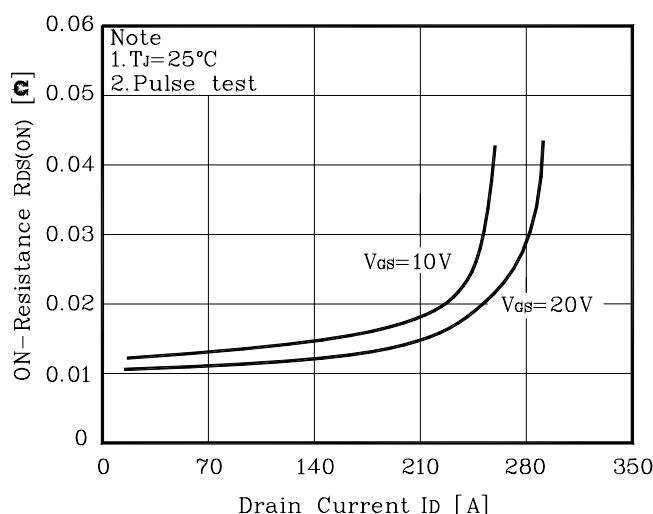


Fig. 4 I_S - V_{SD}

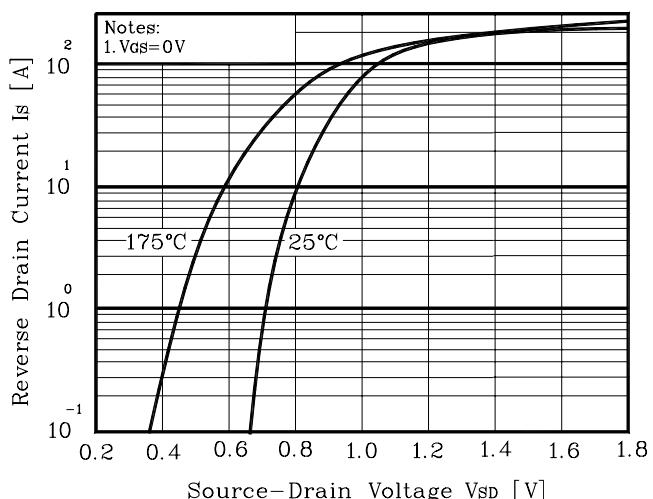


Fig. 5 Capacitance - V_{DS}

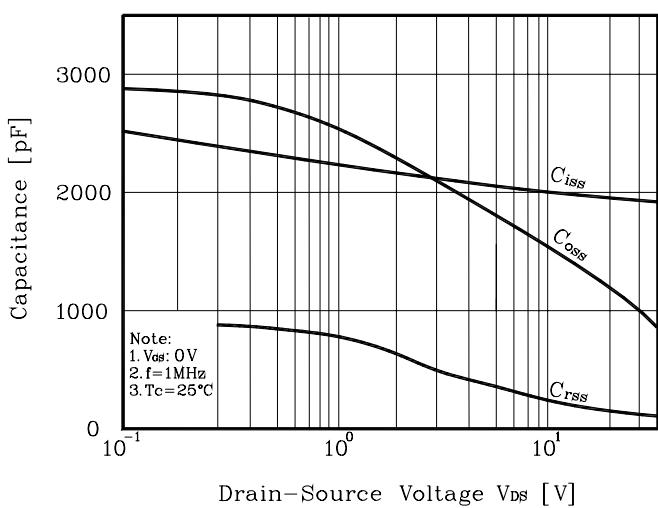


Fig. 6 V_{GS} - Q_G

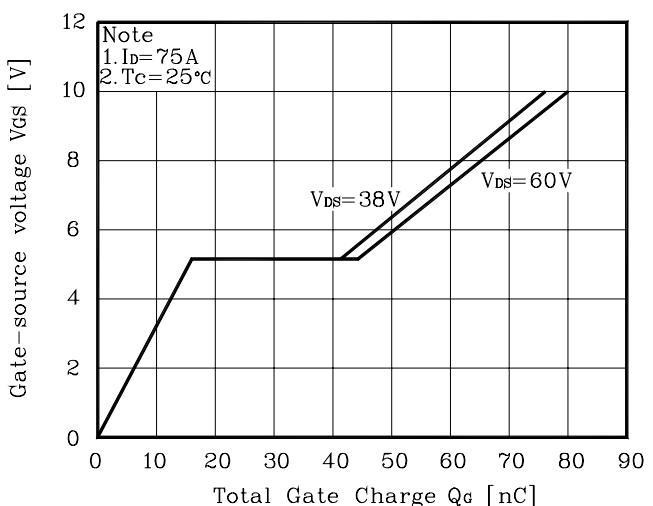


Fig. 7 V_{DSS} - T_J

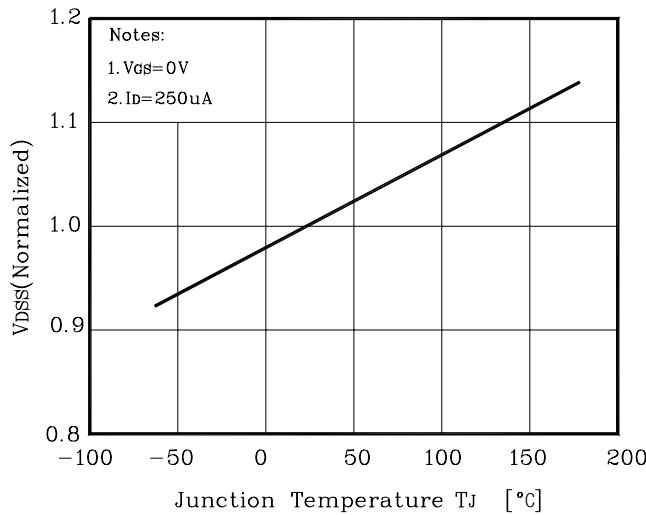


Fig.8 $R_{DS(on)}$ - T_J

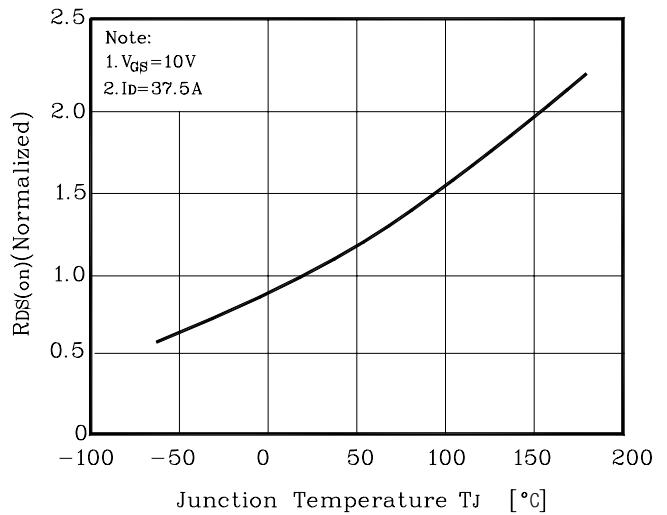


Fig. 9 I_D - T_C

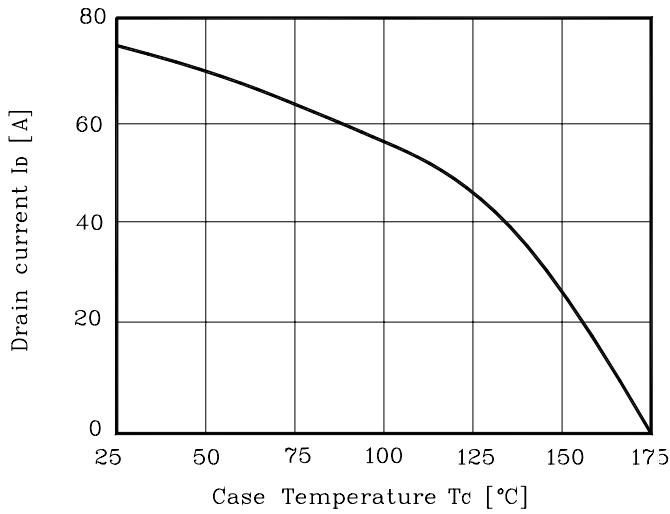


Fig. 10 Safe Operating Area

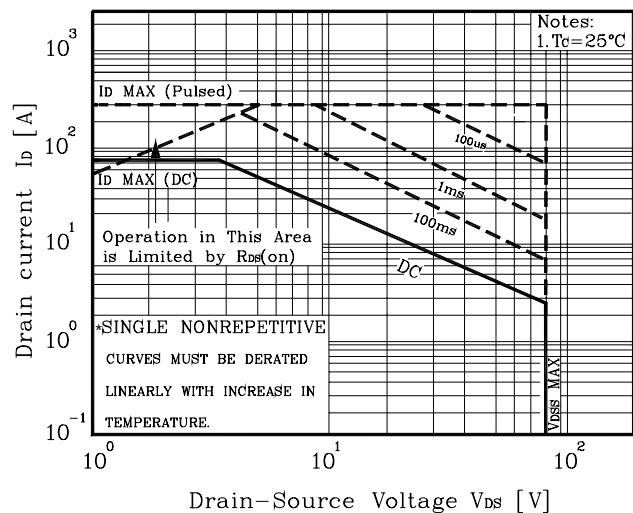


Fig. 10 Gate Charge Test Circuit & Waveform

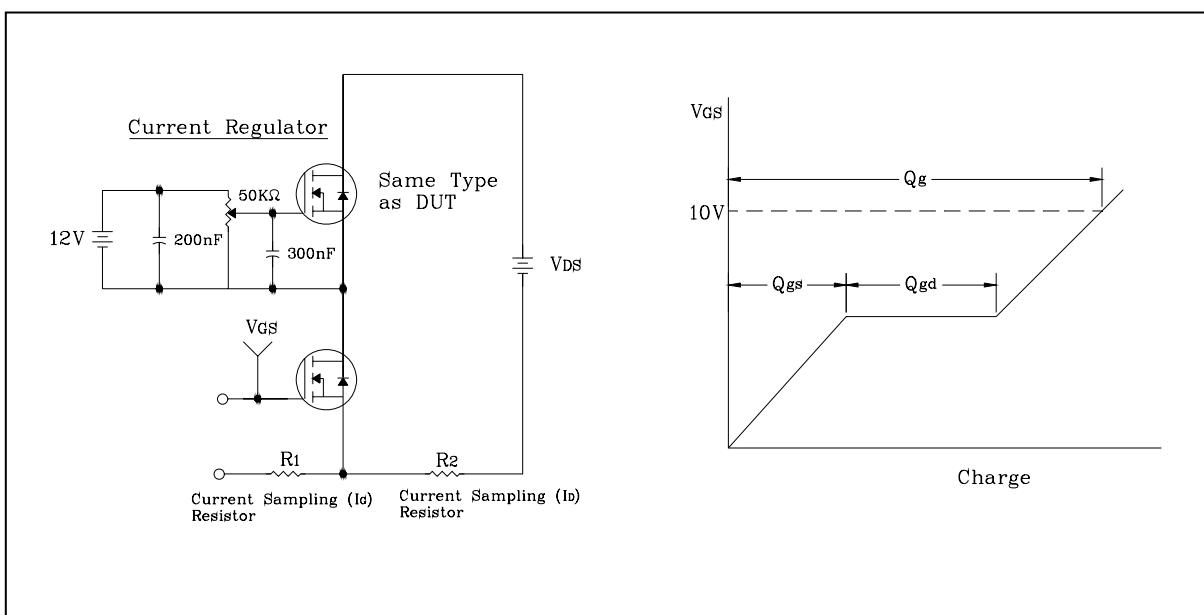


Fig. 11 Resistive Switching Test Circuit & Waveform

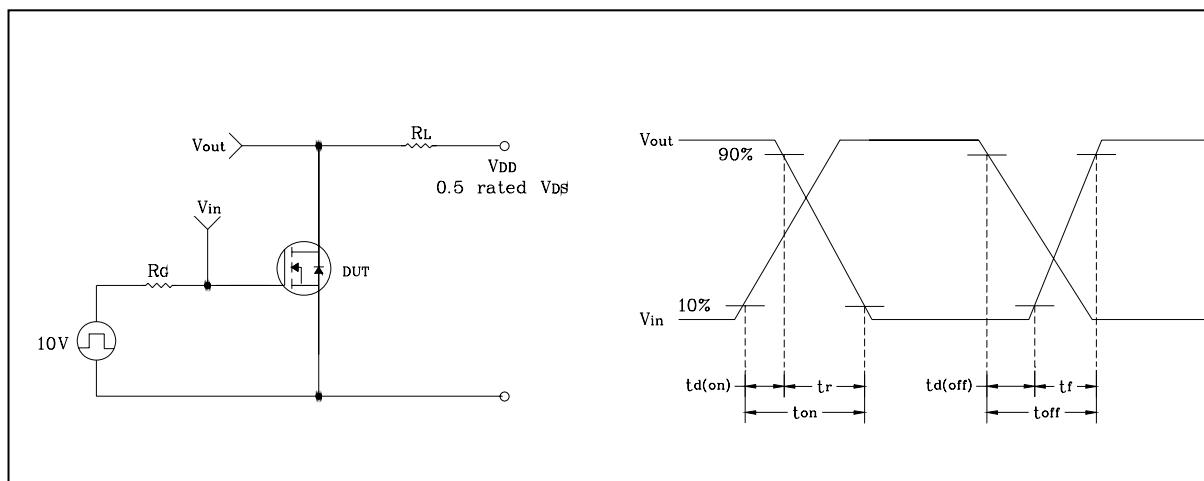


Fig. 12 E_{AS} Test Circuit & Waveform

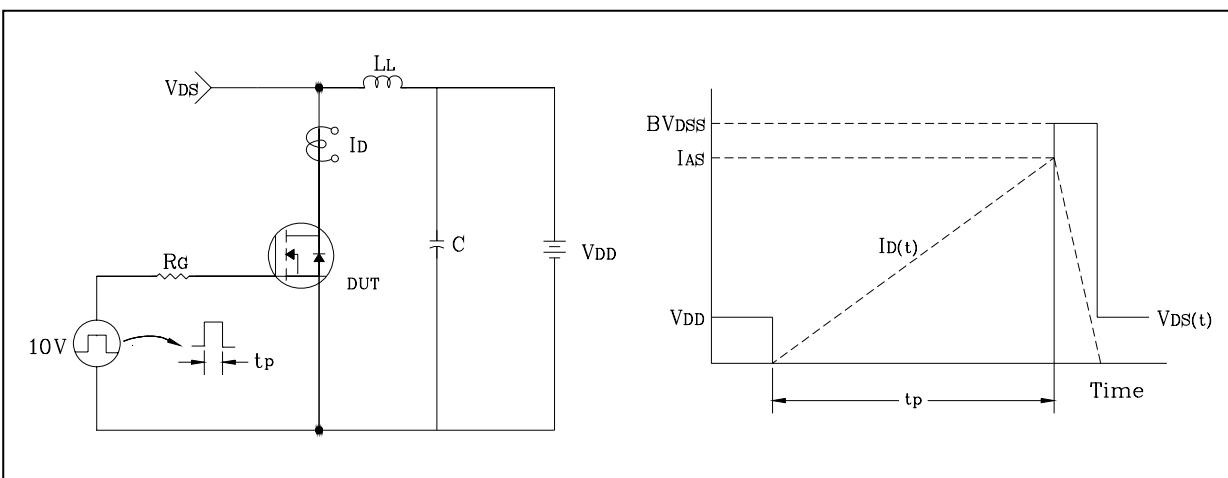
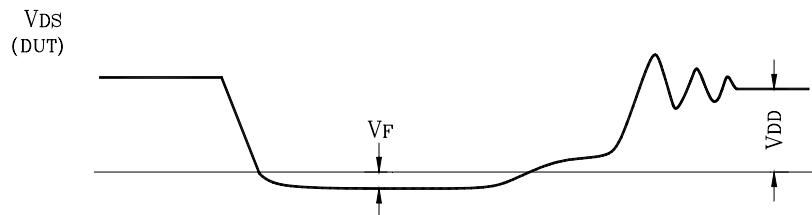
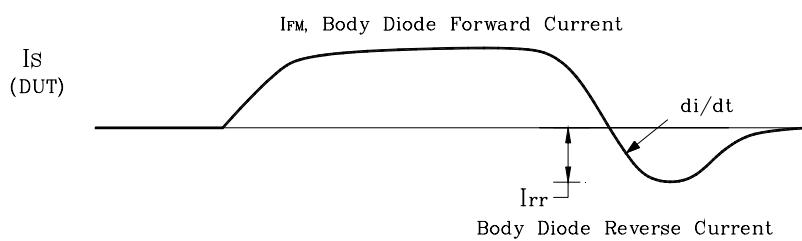
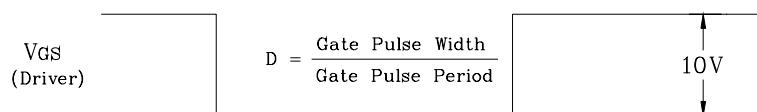
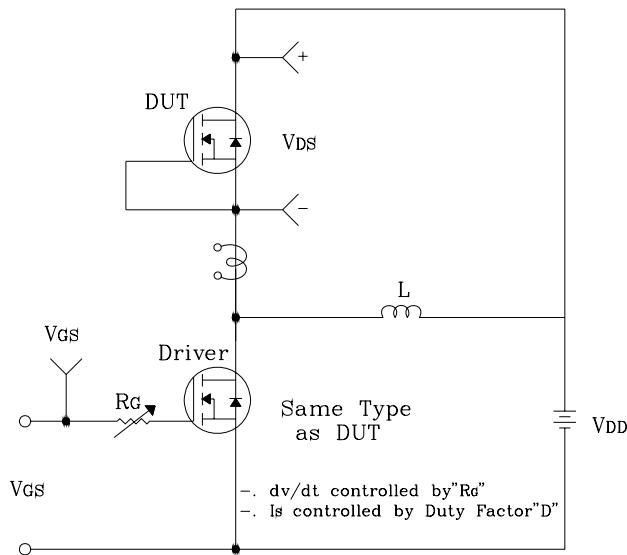


Fig. 13 Diode Reverse Recovery Time Test Circuit & Waveform



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